



JMP(S.Z.F)20N60A

Description

JMP N-channel MOSFET

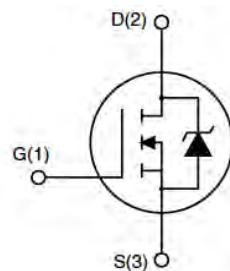
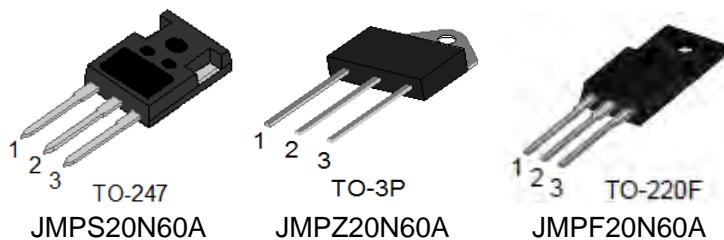
Features

- 600V,20A
- $R_{DS(ON)} = 0.3\Omega$ (Typ.) @ $V_{GS} = 10V$, $I_D = 10A$
- Fast Switching
- Improved dv/dt Capability
- 100% Avalanche Tested

Application

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply(UPS)
- Power Factor Correction (PFC)

Package



Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise specified)

Symbol	Parameter	Max.		Units
		TO-3P/TO-247	TO-220F	
V_{DSS}	Drain-Source Voltage	600		V
V_{GSS}	Gate-Source Voltage	± 30		V
I_D	Continuous Drain Current	20		A
		13		A
I_{DM}	Pulsed Drain Current ^{note1}	80		A
E_{AS}	Single Pulsed Avalanche Energy ^{note2}	1350		mJ
P_D	Power Dissipation	416	167	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	0.3	0.75	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	60	90	$^\circ C/W$
T_J , T_{STG}	Operating and Storage Temperature Range	-55 to +150		$^\circ C$



JMP(S.Z.F)20N60A

Electrical Characteristics ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(\text{BR})\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}, I_D=250\mu\text{A}$	600	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600\text{V}, V_{GS} = 0\text{V}, T_J = 25^\circ\text{C}$	-	-	1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 30\text{V}$	-	-	± 100	nA
On Characteristics						
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D=250\mu\text{A}$	2	3	4	V
$R_{DS(\text{on})}$	Static Drain-Source on-Resistance note3	$V_{GS} = 10\text{V}, I_D = 10\text{A}$	-	0.3	0.45	Ω
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$	-	2980	-	pF
C_{oss}	Output Capacitance		-	291	-	pF
C_{rss}	Reverse Transfer Capacitance		-	40	-	pF
Q_g	Total Gate Charge	$V_{DD} = 480\text{V}, I_D = 20\text{A}, V_{GS} = 10\text{V}$	-	80	-	nC
Q_{gs}	Gate-Source Charge		-	12	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	34	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = 250\text{V}, I_D = 20\text{A}, R_G = 25\Omega$	-	37	-	ns
t_r	Turn-on Rise Time		-	66	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	175	-	ns
t_f	Turn-off Fall Time		-	84	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_s	Maximum Continuous Drain to Source Diode Forward Current	-	-	20	-	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	80	-	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{V}, I_{SD} = 20\text{A}$	-	-	1.4	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{V}, I_s = 20\text{A}, di/dt = 100\text{A}/\mu\text{s}$	-	450	-	ns
Q_{rr}	Reverse Recovery Charge		-	7.1	-	μC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. $I_{AS} = 16\text{A}, V_{DD} = 50\text{V}, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 1\%$



Typical Performance Characteristics

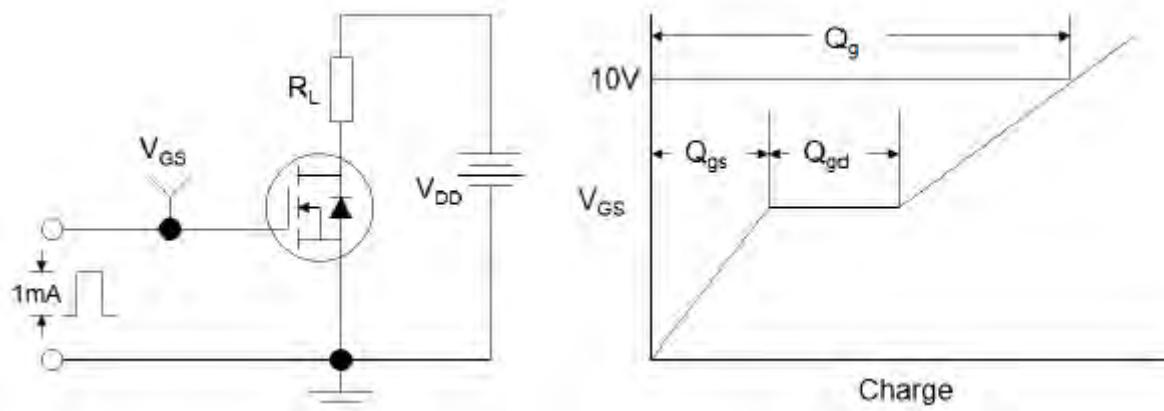


Figure 1: Gate Charge Test Circuit & Waveform

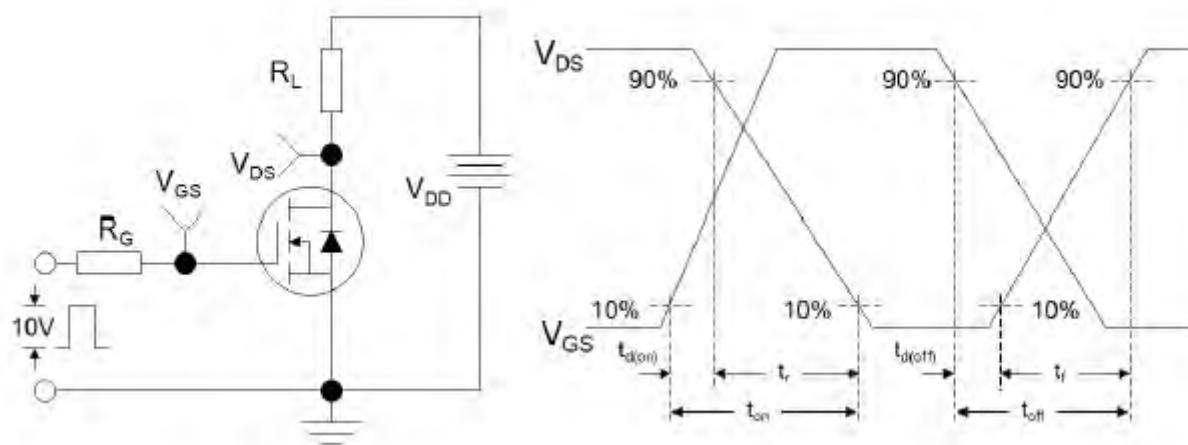


Figure 2: Resistive Switching Test Circuit & Waveforms

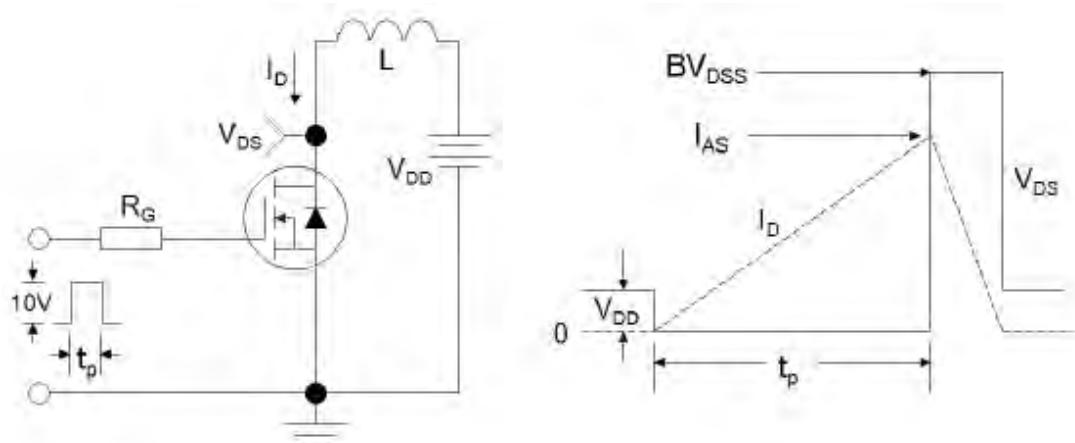


Figure 3: Unclamped Inductive Switching Test Circuit & Waveforms

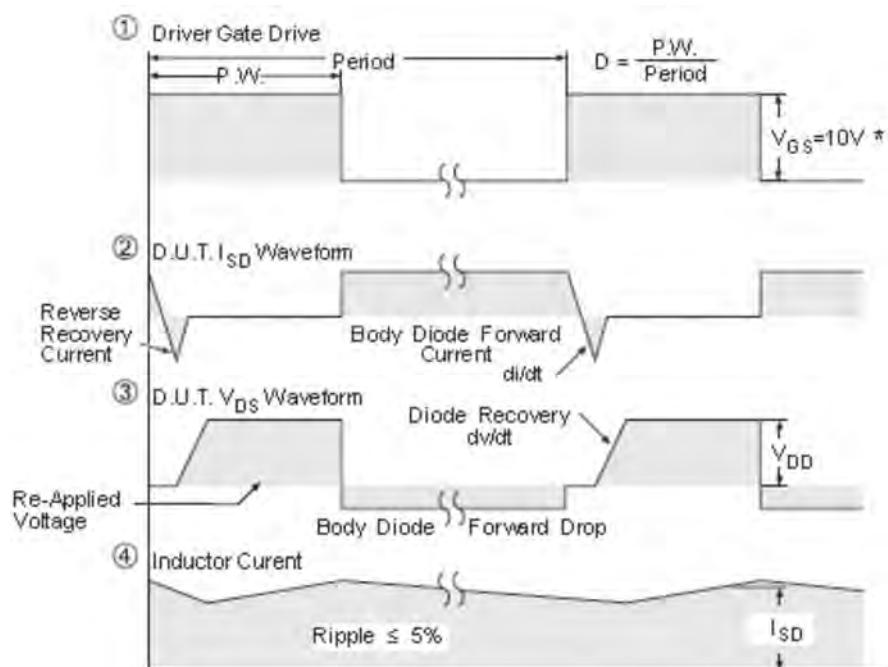
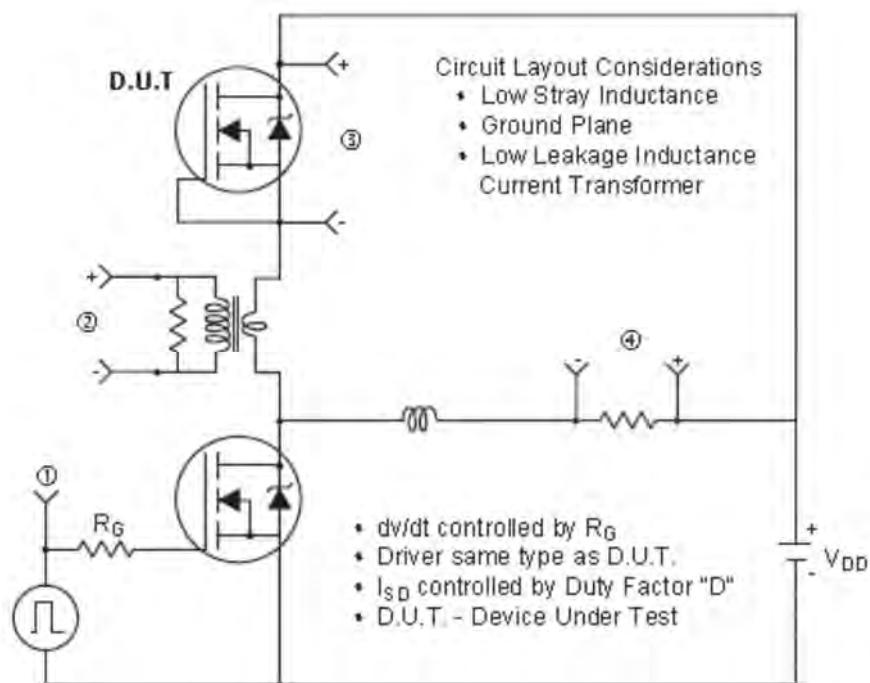
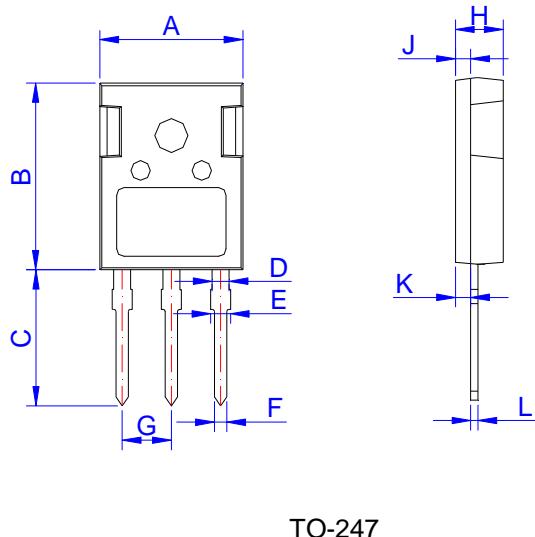


Figure 4:Peak Diode Recovery dv/dt Test Circuit & Waveforms (For N-channel)



Package Mechanical Data



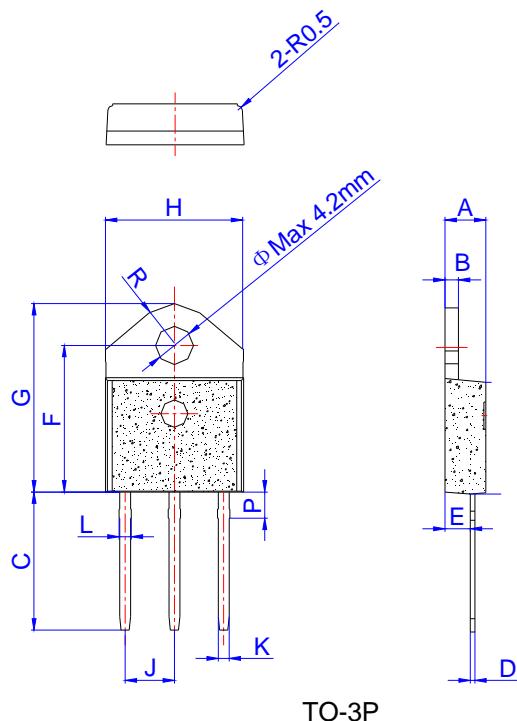
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	15.50	15.80	16.10	0.610	0.622	0.634
B	20.80	21.00	22.20	0.819	0.828	0.874
C	19.70	20.00	20.30	0.776	0.787	0.799
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.90	2.10	2.30	0.075	0.083	0.091
F	1.00	1.20	1.40	0.039	0.047	0.055
G		5.44			0.214	
H	4.80	5.00	5.20	0.189	0.197	0.205
J	1.90	2.00	2.10	0.075	0.079	0.083
K	2.20	2.35	2.50	0.087	0.093	0.098
L	0.41	0.60	0.79	0.016	0.024	0.031

Package Information-TO-247

OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON (PCS)
TUBE	30	450	3,600



Package Mechanical Data



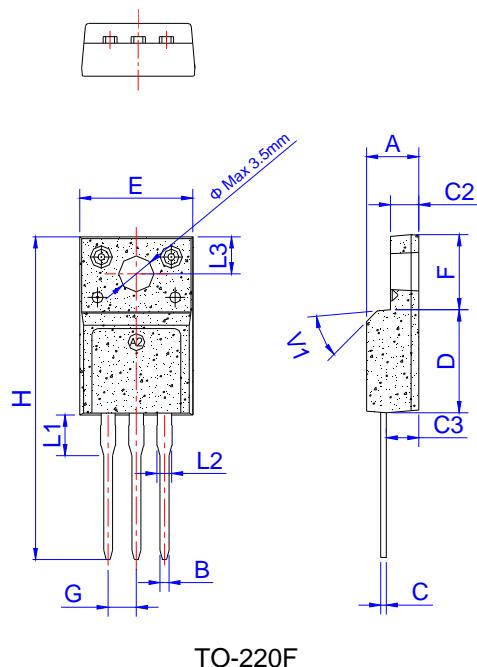
Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.50		0.70	0.020		0.028
E	2.70		2.90	0.106		0.114
F	15.80		16.50	0.622		0.650
G	20.40		21.10	0.803		0.831
H	15.10		15.50	0.594		0.610
J	5.40		5.65	0.213		0.222
K	1.10		1.40	0.043		0.055
L	1.35		1.50	0.053		0.059
P	2.80		3.00	0.110		0.118
R		4.35			0.171	

Package Information- TO-3P

OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON (PCS)
TUBE	30	450	3,600



Package Mechanical Data



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.50		4.90	0.177		0.193
B	0.74	0.80	0.83	0.029	0.031	0.033
C	0.47		0.65	0.019		0.026
C2	2.45		2.75	0.096		0.108
C3	2.60		3.00	0.102		0.118
D	8.80		9.30	0.346		0.366
E	9.80		10.4	0.386		0.410
F	6.40		6.80	0.252		0.268
G		2.54			0.1	
H	28.0		29.8	1.102		1.173
L1		3.63			0.143	
L2	1.14		1.70	0.045		0.067
L3		3.30			0.130	
V1		45°			45°	

Package Information -TO-220F

OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON (PCS)
TUBE	50	1,000	8,000

Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co.,Ltd assumes no responsibility for the consequences of use without consideration for such information nor use beyond it.

Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement.

Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information.

This document is the fourth version which is made in 5-Nov.-2018. This document supersedes and replaces all information previously supplied.

J is a registered trademark of Jiangsu JieJie Microelectronics Co.,Ltd.
Copyright ©2018 Jiangsu JieJie Microelectronics Co.,Ltd. Printed All rights reserved.